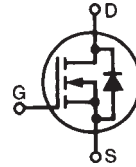


# MegaMOS™ FET

IXTH / IXTM 67N10  
IXTH / IXTM 75N10  
IXTT 75N10

V <sub>DSS</sub>	I <sub>D25</sub>	R <sub>DS(on)</sub>
100 V	67 A	25 mΩ
100 V	75 A	20 mΩ

N-Channel Enhancement Mode



Symbol	Test Conditions	Maximum Ratings	
V <sub>DSS</sub>	T <sub>J</sub> = 25°C to 150°C	100	V
V <sub>DGR</sub>	T <sub>J</sub> = 25°C to 150°C; R <sub>GS</sub> = 1 MΩ	100	V
V <sub>GS</sub>	Continuous	±20	V
V <sub>GSM</sub>	Transient	±30	V
I <sub>D25</sub>	T <sub>C</sub> = 25°C	67N10 75N10	67 75 A
I <sub>DM</sub>	T <sub>C</sub> = 25°C, pulse width limited by T <sub>JM</sub>	67N10 75N10	268 300 A
P <sub>D</sub>	T <sub>C</sub> = 25°C	300	W
T <sub>J</sub>		-55 ... +150	°C
T <sub>JM</sub>		150	°C
T <sub>stg</sub>		-55 ... +150	°C
M <sub>d</sub>	Mounting torque	1.13/10	Nm/lb.in.
Weight		TO-204	18 g
		TO-247	6 g
		TO-268	5 g
Maximum lead temperature for soldering 1.6 mm (0.062 in.) from case for 10 s		10	°C

TO-247 AD (IXTH)

TO-204 AE (IXTM)

TO-268 (IXTT)

G = Gate,  
S = Source,

D = Drain,  
TAB = Drain

### Features

- International standard packages
- Low R<sub>DS(on)</sub> HDMOS™ process
- Rugged polysilicon gate cell structure
- Unclamped Inductive Switching (UIS) rated
- Low package inductance
  - easy to drive and to protect
- Fast intrinsic Rectifier

### Applications

- DC-DC converters
- Synchronous rectification
- Battery chargers
- Switched-mode and resonant-mode power supplies
- DC choppers
- AC motor control
- Temperature and lighting controls
- Low voltage relays

### Advantages

- Easy to mount with 1 screw (TO-247) (isolated mounting screw hole)
- Space savings
- High power density

Symbol	Test Conditions	Characteristic Values (T <sub>J</sub> = 25°C, unless otherwise specified)		
		min.	typ.	max.
V <sub>DSS</sub>	V <sub>GS</sub> = 0 V, I <sub>D</sub> = 250 μA	100		V
V <sub>GS(th)</sub>	V <sub>DS</sub> = V <sub>GS</sub> , I <sub>D</sub> = 4 mA	2.0		V
I <sub>GSS</sub>	V <sub>GS</sub> = ±20 V <sub>DC</sub> , V <sub>DS</sub> = 0			±100 nA
I <sub>DSS</sub>	V <sub>DS</sub> = 0.8 • V <sub>DSS</sub> V <sub>GS</sub> = 0 V	T <sub>J</sub> = 25°C		250 μA
		T <sub>J</sub> = 125°C		1 mA
R <sub>DS(on)</sub>	V <sub>GS</sub> = 10 V, I <sub>D</sub> = 0.5 I <sub>D25</sub> Pulse test, t ≤ 300 μs, duty cycle d ≤ 2 %	67N10		0.025 Ω
		75N10		0.020 Ω

IXYS reserves the right to change limits, test conditions, and dimensions.

DS91533F(9/03)

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$g_{fs}$	$V_{DS} = 10\text{ V}; I_D = I_{D25}$ , pulse test	25	30	S	
$C_{iss}$	$V_{GS} = 0\text{ V}, V_{DS} = 25\text{ V}, f = 1\text{ MHz}$		4500	pF	
$C_{oss}$			1300	pF	
$C_{rss}$			550	pF	
$t_{d(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$ $R_G = 2\ \Omega$ , (External)		40	60	ns
$t_r$			60	110	ns
$t_{d(off)}$			100	140	ns
$t_f$			30	60	ns
$Q_{g(on)}$	$V_{GS} = 10\text{ V}, V_{DS} = 0.5 \cdot V_{DSS}, I_D = 0.5 I_{D25}$		180	260	nC
$Q_{gs}$			30	70	nC
$Q_{gd}$			90	160	nC
$R_{thJC}$	(TO-204, TO-247)			0.42	K/W
$R_{thCK}$			0.25		K/W

**Source-Drain Diode**

Symbol	Test Conditions	Characteristic Values ( $T_J = 25^\circ\text{C}$ , unless otherwise specified)			
		min.	typ.	max.	
$I_S$	$V_{GS} = 0\text{ V}$	67N10 75N10		67 75	A A
$I_{SM}$	Repetitive; pulse width limited by $T_{JM}$	67N10 75N10		268 300	A A
$V_{SD}$	$I_F = I_S, V_{GS} = 0\text{ V}$ , Pulse test, $t \leq 300\ \mu\text{s}$ , duty cycle $d \leq 2\%$			1.75	V
$t_{rr}$	$I_F = I_S, -di/dt = 100\text{ A}/\mu\text{s}, V_R = 100\text{ V}$		200		ns

**TO-247 AD (IXTH) Outline**

Terminals: 1 - Gate 2 - Drain  
3 - Source Tab - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	4.7	5.3	.185	.209
A <sub>1</sub>	2.2	2.54	.087	.102
A <sub>2</sub>	2.2	2.6	.059	.098
b	1.0	1.4	.040	.055
b <sub>1</sub>	1.65	2.13	.065	.084
b <sub>2</sub>	2.87	3.12	.113	.123
C	.4	.8	.016	.031
D	20.80	21.46	.819	.845
E	15.75	16.26	.610	.640
e	5.20	5.72	0.205	0.225
L	19.81	20.32	.780	.800
L <sub>1</sub>		4.50		.177
ØP	3.55	3.65	.140	.144
Q	5.89	6.40	0.232	0.252
R	4.32	5.49	.170	.216
S	6.15	BSC	242	BSC

**TO-204AE (IXTM) Outline**

Pins 1 - Gate 2 - Source  
Case - Drain

Dim.	Millimeter		Inches	
	Min.	Max.	Min.	Max.
A	6.4	11.4	.250	.450
A <sub>1</sub>		3.42		.135
Øb	.97	1.09	.038	.043
ØD		22.22		.875
e	10.67	11.17	.420	.440
e <sub>1</sub>	5.21	5.71	.205	.225
L	7.93		.312	
Øp	3.84	4.19	.151	.165
Øp <sub>1</sub>	3.84	4.19	.151	.165
q	30.15	BSC	1.187	BSC
R		13.33		.525
R <sub>1</sub>		4.77		.188
s	16.64	17.14	.655	.675

**TO-268 (IXTT) Outline**

SYM	INCHES		MILLIMETERS	
	MIN	MAX	MIN	MAX
A	.193	.201	4.90	5.10
A <sub>1</sub>	.106	.114	2.70	2.90
A <sub>2</sub>	.001	.010	0.02	0.25
b	.045	.057	1.15	1.45
b <sub>2</sub>	.075	.083	1.90	2.10
C	.016	.026	0.40	0.65
C <sub>2</sub>	.057	.063	1.45	1.60
D	.543	.551	13.80	14.00
D <sub>1</sub>	.488	.500	12.40	12.70
E	.624	.632	15.85	16.05
E <sub>1</sub>	.524	.535	13.30	13.60
e	.215 BSC		5.45 BSC	
H	.736	.752	18.70	19.10
L	.094	.106	2.40	2.70
L <sub>1</sub>	.047	.055	1.20	1.40
L <sub>2</sub>	.039	.045	1.00	1.15
L <sub>3</sub>	.010	BSC	0.25	BSC
L <sub>4</sub>	.150	.161	3.80	4.10

Fig. 1 Output Characteristics

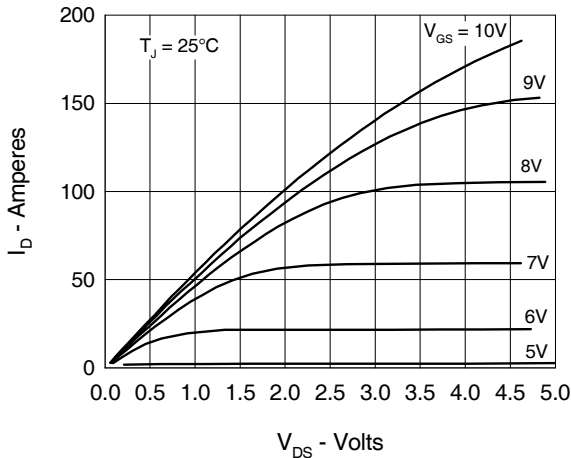


Fig. 2 Input Admittance

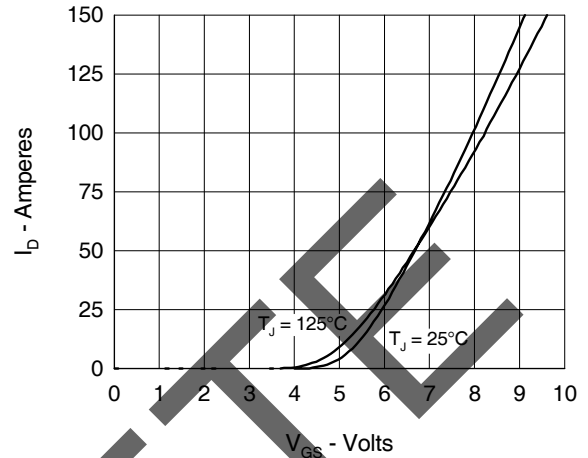


Fig. 3  $R_{DS(on)}$  vs. Drain Current

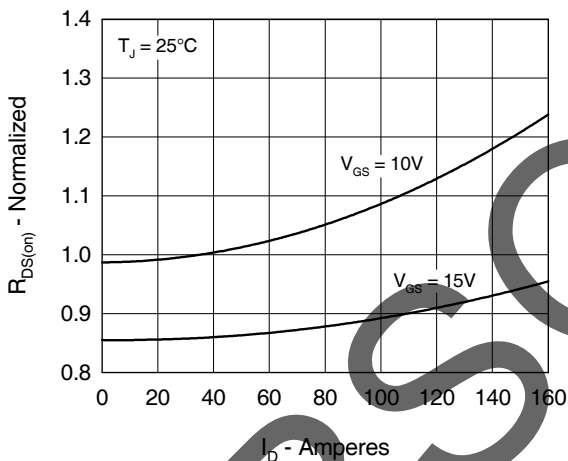


Fig. 4 Temperature Dependence of Drain to Source Resistance

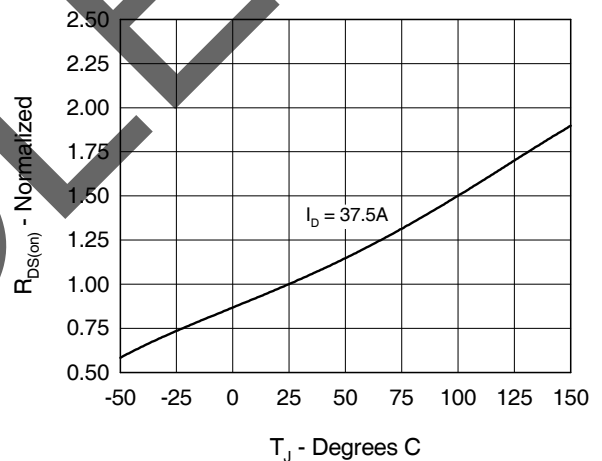


Fig. 5 Drain Current vs. Case Temperature

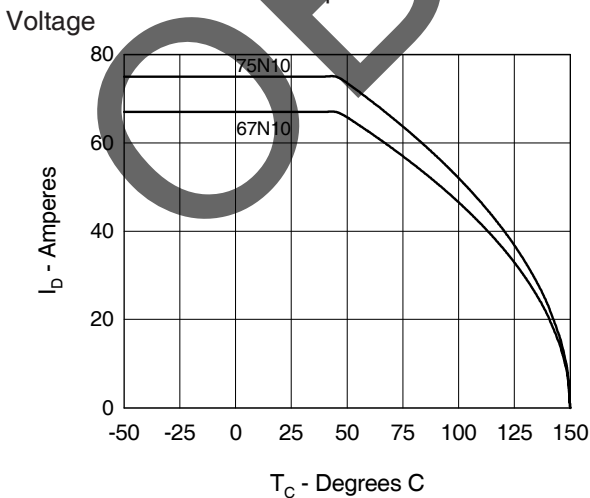
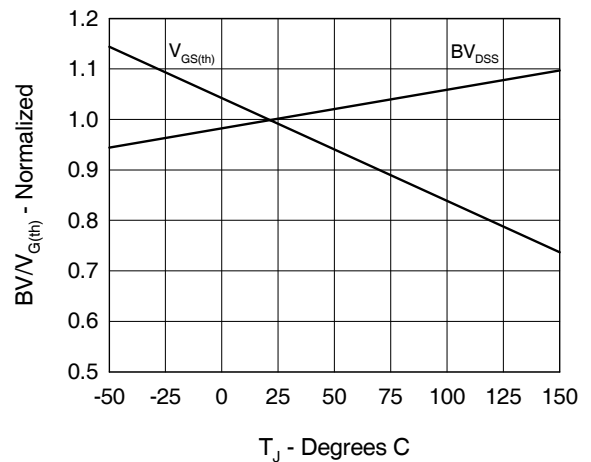
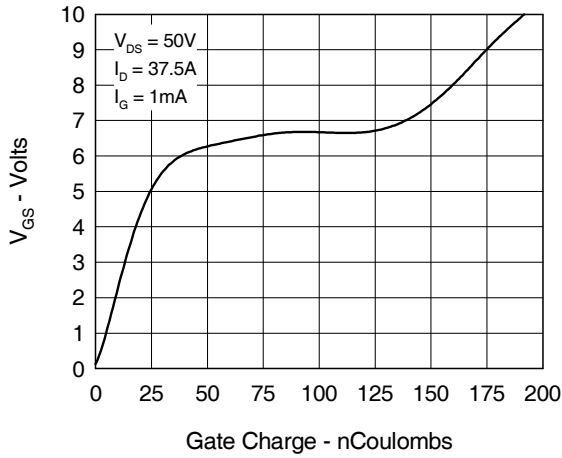


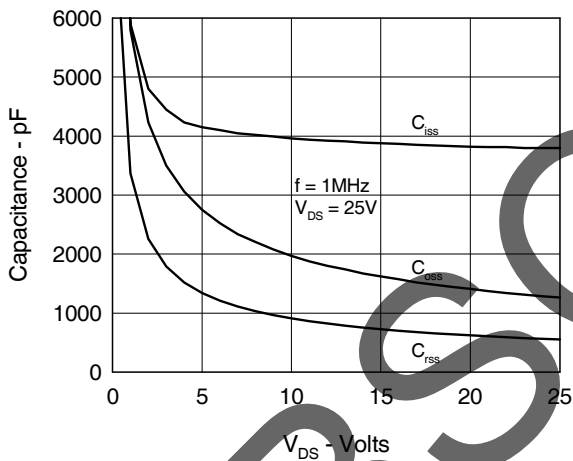
Fig. 6 Temperature Dependence of Breakdown and Threshold



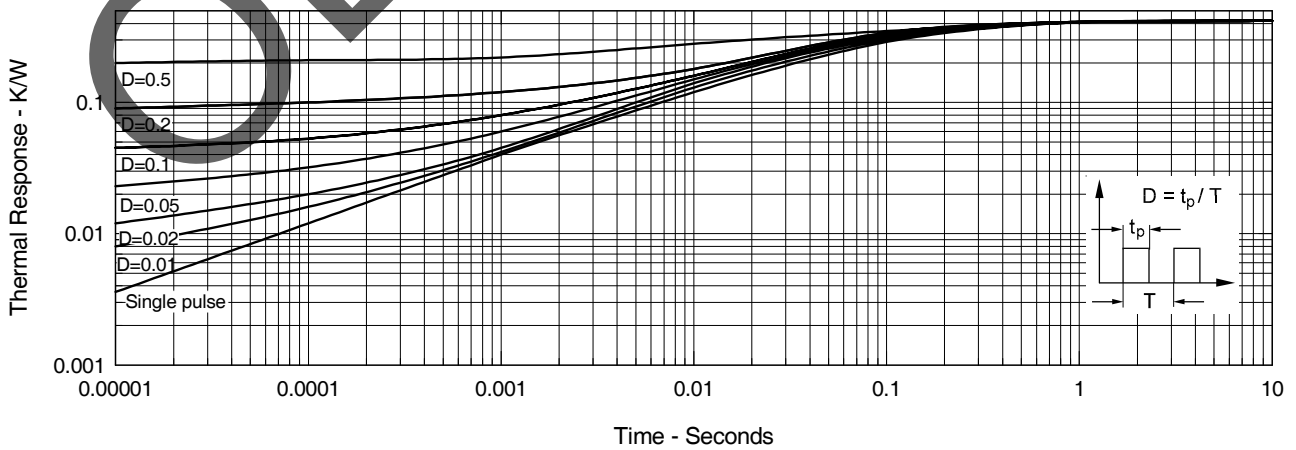
**Fig.7 Gate Charge Characteristic Curve**



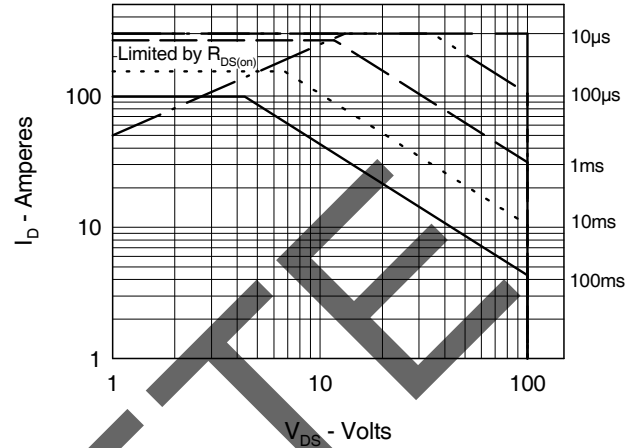
**Fig.9 Capacitance Curves**



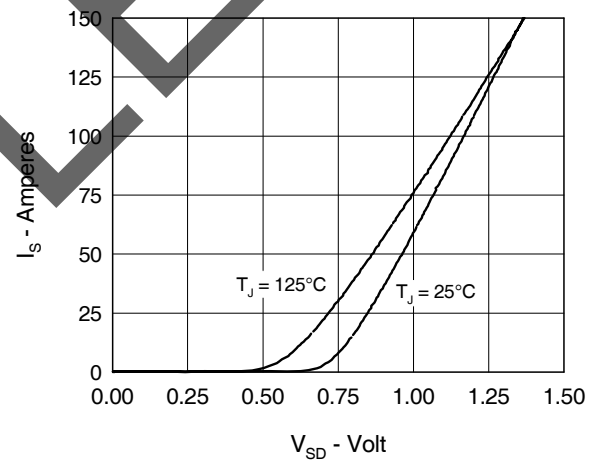
**Fig.11 Transient Thermal Impedance**



**Fig.8 Forward Bias Safe Operating Area**



**Fig.10 Source Current vs. Source to Drain Voltage**





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